

## SN74AHCT367 Hex Buffer and Line Driver with 3-State Output

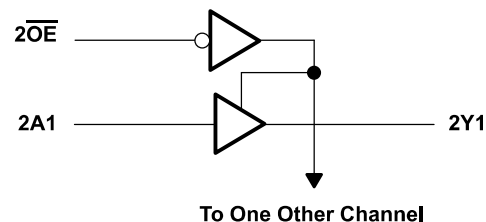
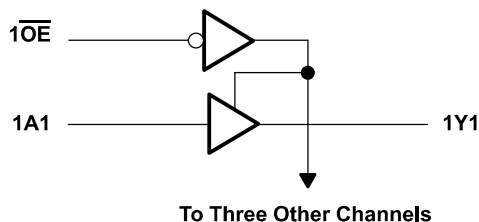
### 1 Features

- Inputs are TTL-Voltage Compatible
- True Outputs
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model
  - 200-V Machine Model
  - 2000-V Charged-Device Model

### 2 Applications

- Telecom Infrastructure
- TVs
- Set Top Boxes
- Network Switches
- Wireless Infrastructure
- Electronic Points of Sale

### 4 Simplified Schematic



### 3 Description

The SN74AHCT367 device is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74AHCT367	PDIP (16)	19.30 mm x 6.35 mm
	SSOP (16)	6.50 mm x 5.30 mm
	TSSOP (16)	5.00 mm x 4.40 mm
	SOP (16)	10.20 mm x 5.30 mm
	SOIC (16)	9.00 mm x 3.90 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



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## 5 Revision History

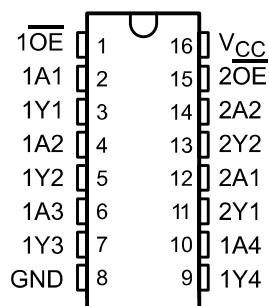
### Changes from Revision G (July 2003) to Revision H

Page

<ul style="list-style-type: none"> <li>• Added <i>Applications</i>, <i>Device Information</i> table, <i>Pin Functions</i> table, <i>ESD Ratings</i> table, <i>Thermal Information</i> table, <i>Typical Characteristics</i>, <i>Feature Description</i> section, <i>Device Functional Modes</i>, <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section. .... 1</li> <li>• Deleted <i>Ordering Information</i> table. .... 1</li> <li>• MAX operating temperature to 125°C in <i>Recommended Operating Conditions</i> table. .... 4</li> </ul>	<p>1</p> <p>1</p> <p>4</p>
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## 6 Pin Configuration and Functions

SN74AHCT367 . . . D, DB, DGV, OR PW PACKAGE  
(TOP VIEW)



**Pin Functions**

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	$\overline{1OE}$	I	Output Enable 1
2	1A1	I	1A1 Input
3	1Y1	O	1Y1 Output
4	1A2	I	1A2 Input
5	1Y2	O	1Y2 Output
6	1A3	I	1A3 Input
7	1Y3	O	1Y3 Output
8	GND	—	Ground Pin
9	1Y4	O	1Y4 Output
10	1A4	I	1A4 Input
11	2Y1	O	2Y1 Output
12	2A1	I	2A1 Input
13	2Y2	O	2Y2 Output
14	2A2	I	2A2 Input
15	$\overline{2OE}$	I	Output Enable 2
16	V <sub>CC</sub>	—	Power Pin

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
$V_{CC}$	Supply voltage range	−0.5	7	V
$V_I$	Input voltage range <sup>(2)</sup>	−0.5	7	V
$V_O$	Output voltage range <sup>(2)</sup>	−0.5	$V_{CC} + 0.5$	V
$I_{IK}$	Input clamp current	$V_I < 0$	−20	mA
$I_{OK}$	Output clamp current	$V_O < 0$ or $V_O > V_{CC}$	±20	mA
$I_O$	Continuous output current	$V_O = 0$ to $V_{CC}$	±25	mA
	Continuous current through $V_{CC}$ or GND		±75	mA
$T_{stg}$	Storage temperature range	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 7.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge		
	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	2000	V
Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	2000		

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		SN74AHCT367		UNIT
		MIN	MAX	
$V_{CC}$	Supply voltage	4.5	5.5	V
$V_{IH}$	High-level input voltage	2		V
$V_{IL}$	Low-level Input voltage		0.8	V
$V_I$	Input voltage	0	5.5	V
$V_O$	Output voltage	0	$V_{CC}$	V
$I_{OH}$	High-level output current		−8	mA
$I_{OL}$	Low-level output current		8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		20	ns/V
$T_A$	Operating free-air temperature	−40	125	°C

- (1) All unused inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs (SCBA004)*.

## 7.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		SN74AHCT367				UNIT
		D	DB	DGV	PW	
		16 PINS				
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	85.1	103.9	124.5	111.5	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	46.5	54.3	49.8	46.5	
R <sub>θJB</sub>	Junction-to-board thermal resistance	42.6	54.6	56.2	56.6	
ψ <sub>JT</sub>	Junction-to-top characterization parameter	13.2	14.3	5.8	5.8	
ψ <sub>JB</sub>	Junction-to-board characterization parameter	42.4	54.0	55.7	56.0	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

## 7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	T <sub>A</sub> = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V <sub>OH</sub>	I <sub>OH</sub> = –50 μA	4.5 V	4.4	4.5		4.4		4.4	V	
	I <sub>OH</sub> = –8 mA		3.94			3.8		3.8		
V <sub>OL</sub>	I <sub>OL</sub> = 50 μA	4.5 V			0.1		0.1	0.1	V	
	I <sub>OH</sub> = 8 mA			0.36		0.44		0.44		
I <sub>I</sub>	V <sub>I</sub> = 5.5 V or GND	0 V to 5.5 V			±0.1 <sup>(1)</sup>		±1 <sup>(1)</sup>	±1	μA	
I <sub>OZ</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND V <sub>I</sub> (OE) = V <sub>IL</sub> or V <sub>IH</sub>	5.5 V			±0.25		±2.5	±2.5	μA	
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0	5.5 V			4		40	40	μA	
ΔI <sub>CC</sub> <sup>(2)</sup>	One input at 3.4 V, Other inputs at V <sub>CC</sub> or GND	5.5 V			1.35		1.5	1.5	mA	
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	5 V		2.5	10		10	10	pF	
C <sub>O</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5 V		5					pF	

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested at V<sub>CC</sub> = 0 V.

(2) This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V<sub>CC</sub>.

## 7.6 Switching Characteristics

over recommended operating free-air temperature range, V<sub>CC</sub> = 5 V ± 0.5 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T <sub>A</sub> = 25°C		–40°C to 85°C		–40°C to 125°C		UNIT
				TYP	MAX	MIN	MAX	MIN	MAX	
t <sub>PLH</sub>	A	Y	C <sub>L</sub> = 15 pF	2.5 <sup>(1)</sup>	4.8 <sup>(1)</sup>	1	6.5	1	8.5	ns
t <sub>PHL</sub>				2.5 <sup>(1)</sup>	4.8 <sup>(1)</sup>	1	6.5	1	8.5	
t <sub>PZH</sub>	OE	Y	C <sub>L</sub> = 15 pF	3.5 <sup>(1)</sup>	8 <sup>(1)</sup>	1	9.5	1	9	ns
t <sub>PZL</sub>				2.8 <sup>(1)</sup>	7 <sup>(1)</sup>	1	8.5 <sup>(1)</sup>	1	8	
t <sub>PHZ</sub>	OE	Y	C <sub>L</sub> = 15 pF	3.1 <sup>(1)</sup>	8 <sup>(1)</sup>	1	9.5	1	9	ns
t <sub>PLZ</sub>				2.8 <sup>(1)</sup>	7 <sup>(1)</sup>	1	8.5	1	8	
t <sub>PLH</sub>	A	Y	C <sub>L</sub> = 50 pF	3.5	5.8	1	7.5	1	9.5	ns
t <sub>PHL</sub>				3.3	5.8	1	7.5	1	9.5	
t <sub>PZH</sub>	OE	Y	C <sub>L</sub> = 50 pF	4.5	9	1	10.5	1	10	ns
t <sub>PZL</sub>				3.7	8	1	9.5	1	9	
t <sub>PHZ</sub>	OE	Y	C <sub>L</sub> = 50 pF	4.1	9	1	10.5	1	10	ns
t <sub>PLZ</sub>				3.6	8	1	9.5	1	9	

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

### 7.7 Noise Characteristics

$V_{CC} = 5\text{ V}$ ,  $C_L = 50\text{ pF}$ ,  $T_A = 25^\circ\text{C}^{(1)}$

PARAMETER		SN74AHCT367			UNIT
		MIN	TYP	MAX	
$V_{OL(P)}$	Quiet output, maximum dynamic $V_{OL}$		0.4		V
$V_{OL(V)}$	Quiet output, minimum dynamic $V_{OL}$		-0.4		V
$V_{OH(V)}$	Quiet output, minimum dynamic $V_{OH}$		4.7		V
$V_{IH(D)}$	High-level dynamic input voltage	2			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

(1) Characteristics are for surface-mount packages only.

### 7.8 Operating Characteristics

$V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TYP	UNIT
$C_{pd}$	Power dissipation capacitance No load, $f = 1\text{ MHz}$	22	pF

### 7.9 Typical Characteristics

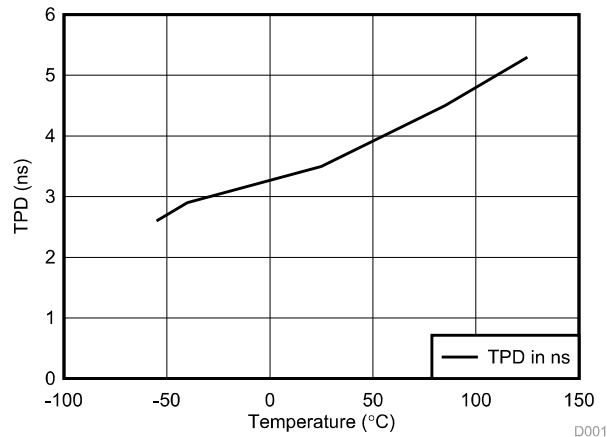
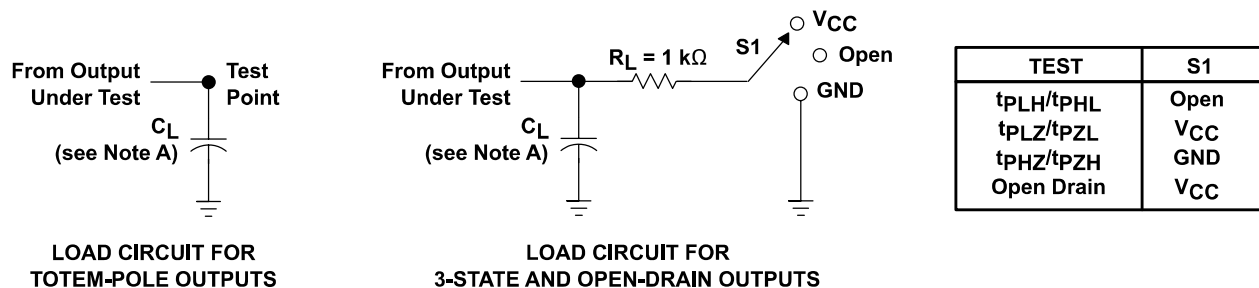


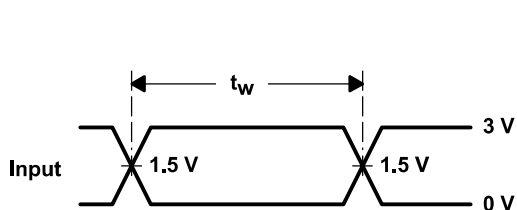
Figure 1. TPD vs Temperature, 50 pF Load

## 8 Parameter Measurement Information

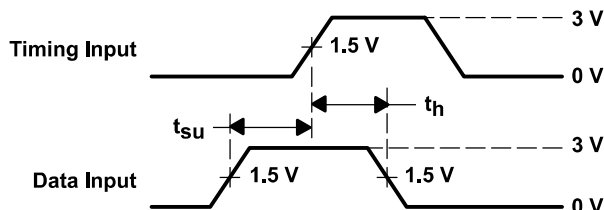


LOAD CIRCUIT FOR TOTEM-POLE OUTPUTS

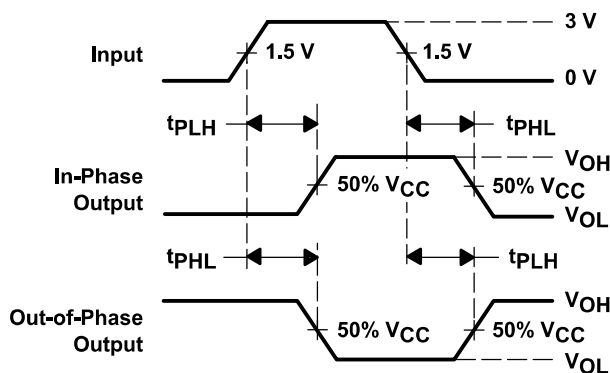
LOAD CIRCUIT FOR 3-STATE AND OPEN-DRAIN OUTPUTS



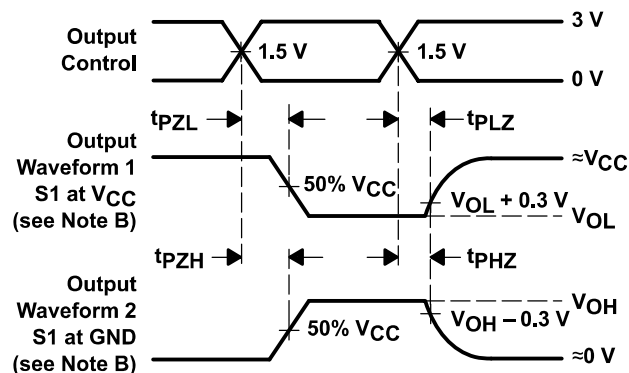
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.  
 C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1$  MHz,  $Z_O = 50 \Omega$ ,  $t_r \leq 3$  ns,  $t_f \leq 3$  ns.  
 D. The outputs are measured one at a time with one input transition per measurement.  
 E. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

## 9 Detailed Description

### 9.1 Overview

The SN74AHCT367 device is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. This device is organized as a dual 4-line and 2-line buffer/driver with active-low output-enable ( $1\overline{OE}$  and  $2\overline{OE}$ ) inputs. When  $\overline{OE}$  is low, the device passes noninverted data from the A inputs to the Y outputs. When  $\overline{OE}$  is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

### 9.2 Functional Block Diagram



**Figure 3. Logic Diagram (Positive Logic)**

### 9.3 Feature Description

- $V_{CC}$  is optimized at 5 V
- Allows up voltage translation from 3.3 V to 5 V
  - Inputs Accept  $V_{IH}$  levels of 2 V
- Slow edge rates minimize output ringing
- Inputs are TTL-Voltage compatible

### 9.4 Device Functional Modes

**Table 1. Function Table  
(Each Buffer/Driver)**

INPUTS		OUTPUT Y
$\overline{OE}$	A	
H	X	Z
L	H	H
L	L	L



## 10 Application and Implementation

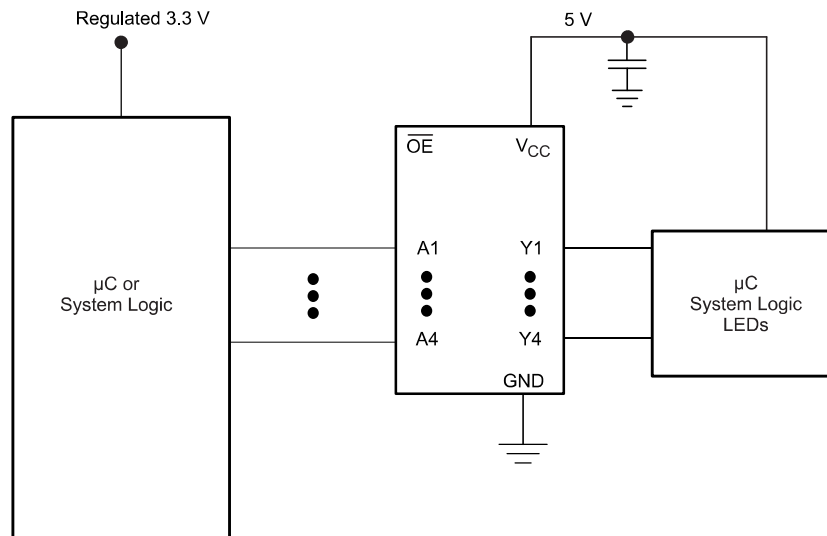
### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 10.1 Application Information

SN74AHCT367 is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The input switching levels have been lowered to accommodate TTL inputs of 0.8-V  $V_{IL}$  and 2-V  $V_{IH}$ . This feature makes it ideal for translating up from 3.3 V to 5 V. [Figure 5](#) shows this type of translation.

### 10.2 Typical Application



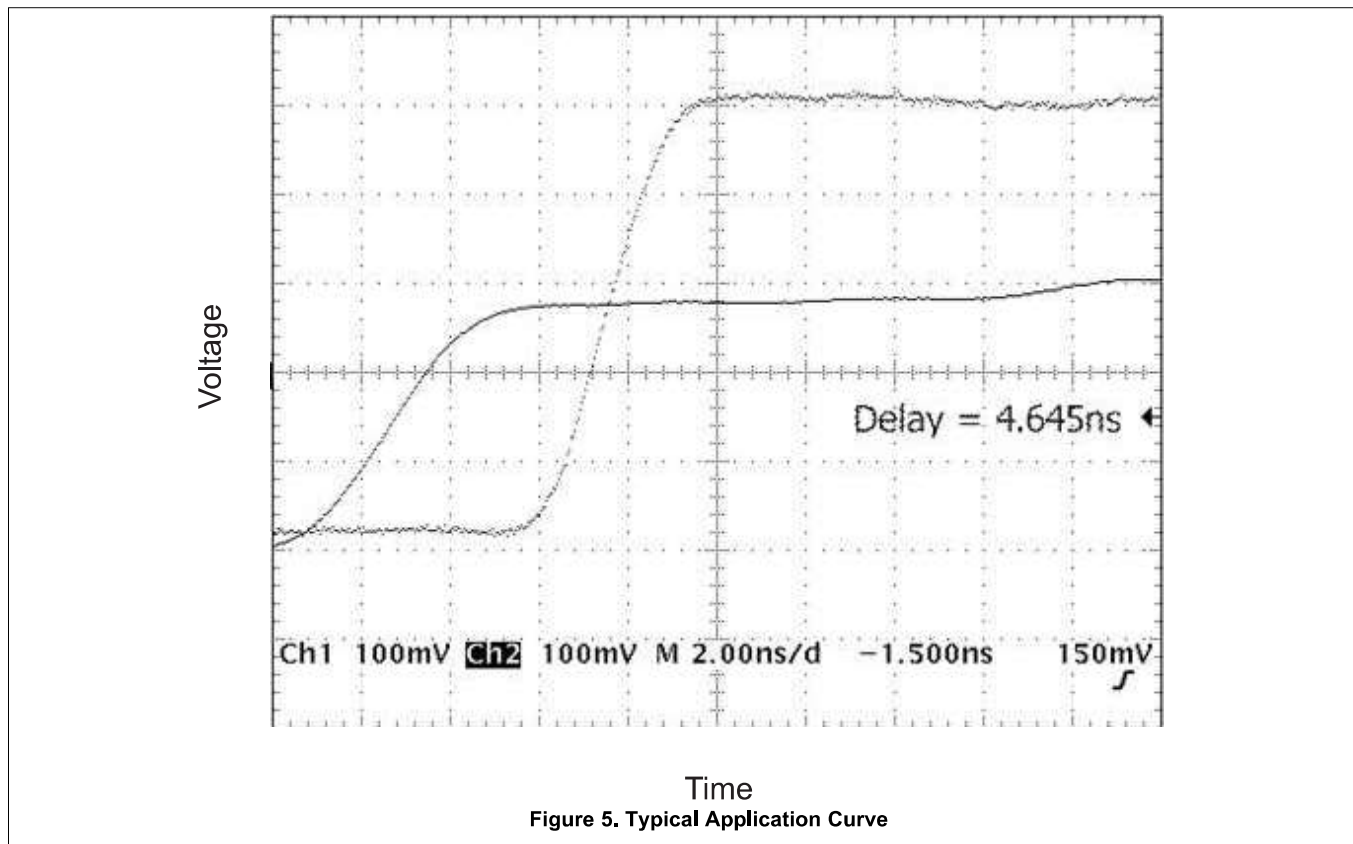
**Figure 4. Typical Application Schematic**

#### 10.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

#### 10.2.2 Detailed Design Procedure

1. Recommended Input Conditions
  - For rise time and fall time specifications, see  $\Delta t/\Delta V$  in the [Recommended Operating Conditions](#) table.
  - For specified High and low levels, see  $V_{IH}$  and  $V_{IL}$  in the [Recommended Operating Conditions](#) table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid  $V_{CC}$ .
2. Recommend Output Conditions
  - Load currents should not exceed 25 mA per output and 75 mA total for the part.
  - Outputs should not be pulled above  $V_{CC}$ .

**Typical Application (continued)**
**10.2.3 Application Curves**

**11 Power Supply Recommendations**

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each  $V_{CC}$  pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1  $\mu\text{F}$  is recommended. If there are multiple  $V_{CC}$  pins, 0.01  $\mu\text{F}$  or 0.022  $\mu\text{F}$  is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1  $\mu\text{F}$  and 1  $\mu\text{F}$  are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

## 12 Layout

### 12.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 6 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

### 12.2 Layout Example

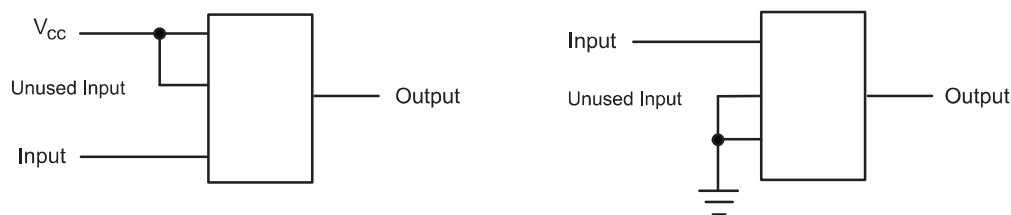


Figure 6. Layout Diagram

## 13 Device and Documentation Support

### 13.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 2. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74AHCT367	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>

### 13.2 Trademarks

All trademarks are the property of their respective owners.

### 13.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 13.4 Glossary

[SLYZ022](#) — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.